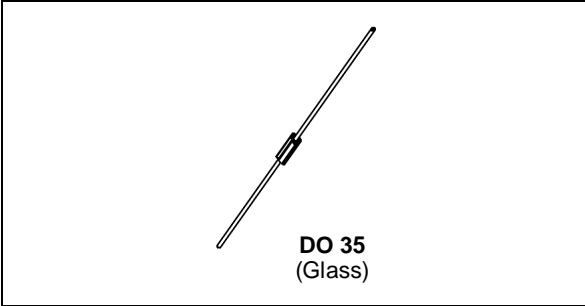


SMALL SIGNAL SCHOTTKY DIODE

DESCRIPTION

General purpose metal to silicon diode featuring very low turn-on voltage and fast switching.

This device has integrated protection against excessive voltage such as electrostatic discharges.



ABSOLUTE RATINGS (limiting values)

| Symbol | Parameter | | Value | Unit |
|--------------------|--|--|------------------------------|--|
| V_{RRM} | Repetitive Peak Reverse Voltage | | 100 | V |
| I_F | Forward Continuous Current* | $T_a = 25\text{ }^{\circ}\text{C}$ | 100 | mA |
| I_{FRM} | Repetitive Peak Forward Current* | $t_p \leq 1\text{ s}$ $\delta \leq 0.5$ | 350 | mA |
| I_{FSM} | Surge non Repetitive Forward Current* | $t_p \leq 10\text{ ms}$ | 750 | mA |
| P_{tot} | Power Dissipation* $T_a = 95^{\circ}\text{C}$ | | 100 | mW |
| T_{stg} T_j | Storage and Junction Temperature Range | | - 65 to +150 - 65 to +125 | $^{\circ}\text{C}$ $^{\circ}\text{C}$ |
| T_L | Maximum Lead Temperature for Soldering during 10s at 4mm from Case | | 230 | $^{\circ}\text{C}$ |

THERMAL RESISTANCE

| Symbol | Test Conditions | Value | Unit |
|---------------|-------------------|-------|----------------------|
| $R_{th(j-a)}$ | Junction-ambient* | 300 | $^{\circ}\text{C/W}$ |

ELECTRICAL CHARACTERISTICS

STATIC CHARACTERISTICS

| Symbol | Test Conditions | | Min. | Typ. | Max. | Unit |
|------------|-----------------------------|------------------------|------|------|------|---------------|
| V_{BR} | $T_j = 25^{\circ}\text{C}$ | $I_R = 100\mu\text{A}$ | 100 | | | V |
| V_F^{**} | $T_j = 25^{\circ}\text{C}$ | $I_F = 1\text{ mA}$ | | 0.4 | 0.45 | V |
| | $T_j = 25^{\circ}\text{C}$ | $I_F = 200\text{ mA}$ | | | 1 | |
| I_R^{**} | $T_j = 25^{\circ}\text{C}$ | $V_R = 50\text{ V}$ | | | 0.1 | μA |
| | $T_j = 100^{\circ}\text{C}$ | | | | 20 | |

DYNAMIC CHARACTERISTICS

| Symbol | Test Conditions | | | Min. | Typ. | Max. | Unit |
|--------|----------------------------|--------------------|--------------------|------|------|------|------|
| C | $T_j = 25^{\circ}\text{C}$ | $V_R = 1\text{ V}$ | $f = 1\text{ MHz}$ | | 2 | | pF |

* On infinite heatsink with 4mm lead length

** Pulse test: $t_p \leq 300\mu\text{s}$ $\delta < 2\%$.

Figure 1. Forward current versus forward voltage at different temperatures (typical values).

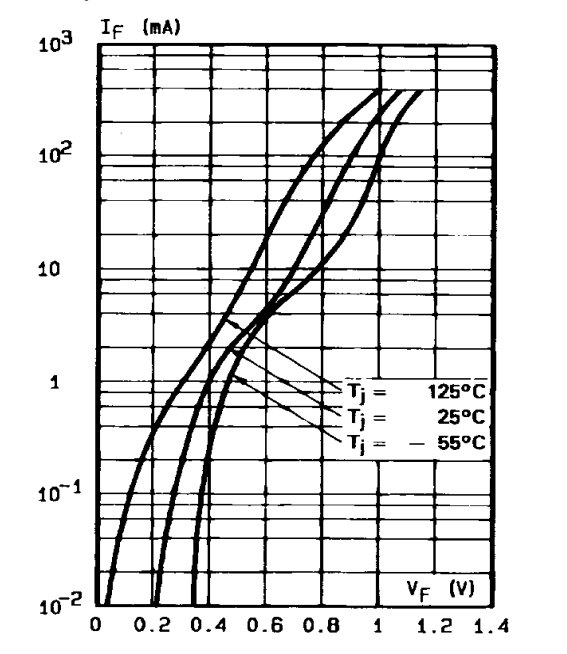


Figure 2. Forward current versus forward voltage (typical values).

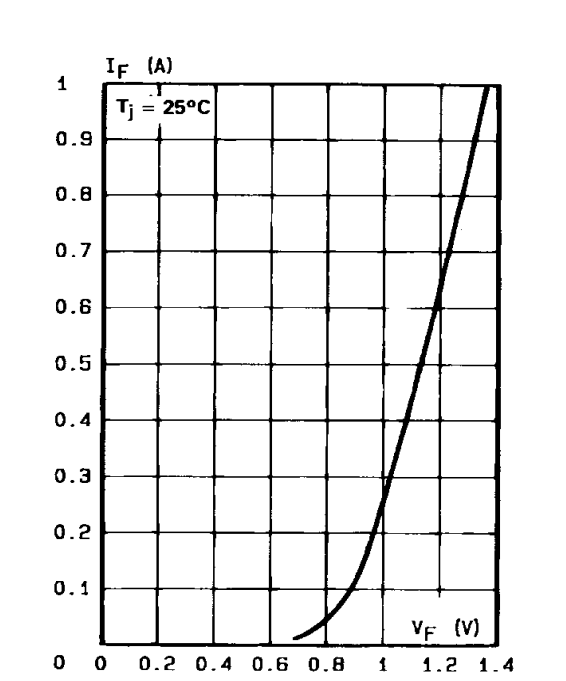


Figure 3. Reverse current versus junction temperature.

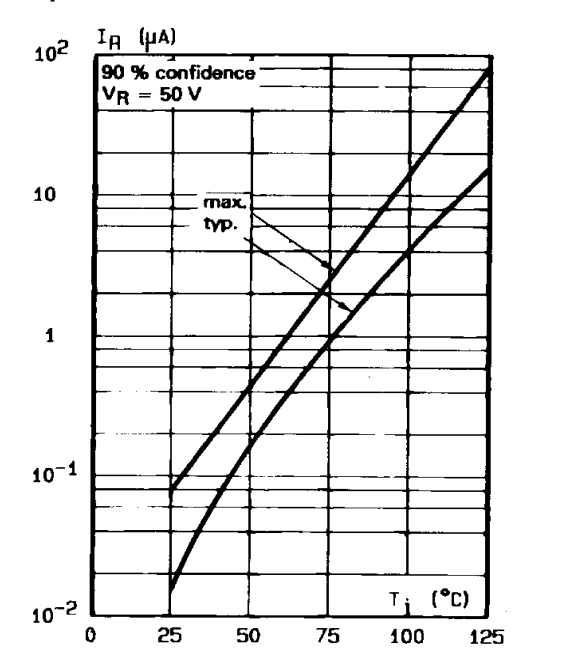


Figure 4. Reverse current versus continuous reverse voltage (typical values).

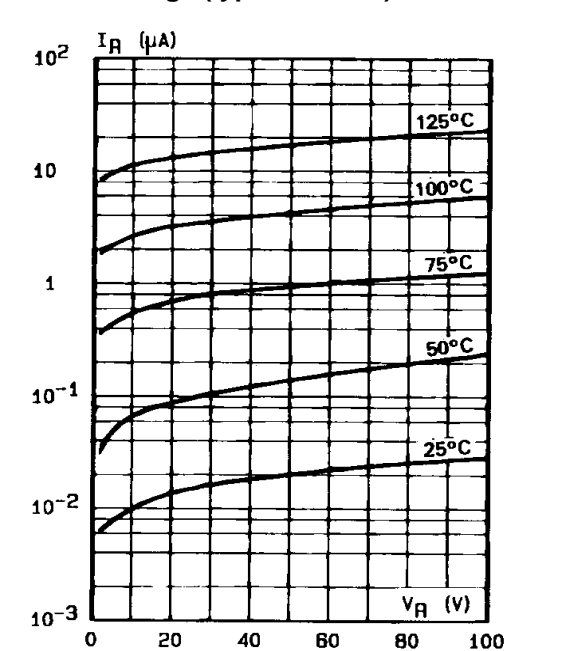
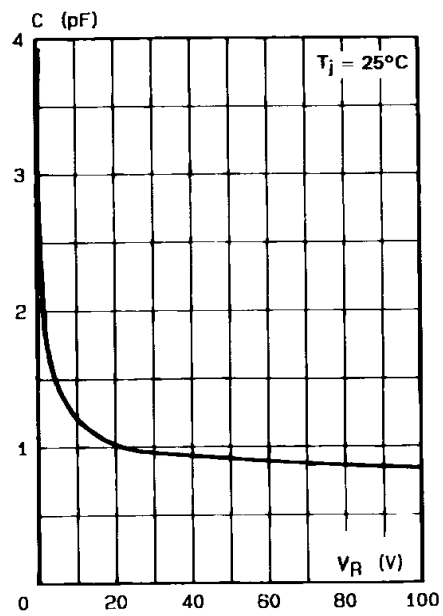


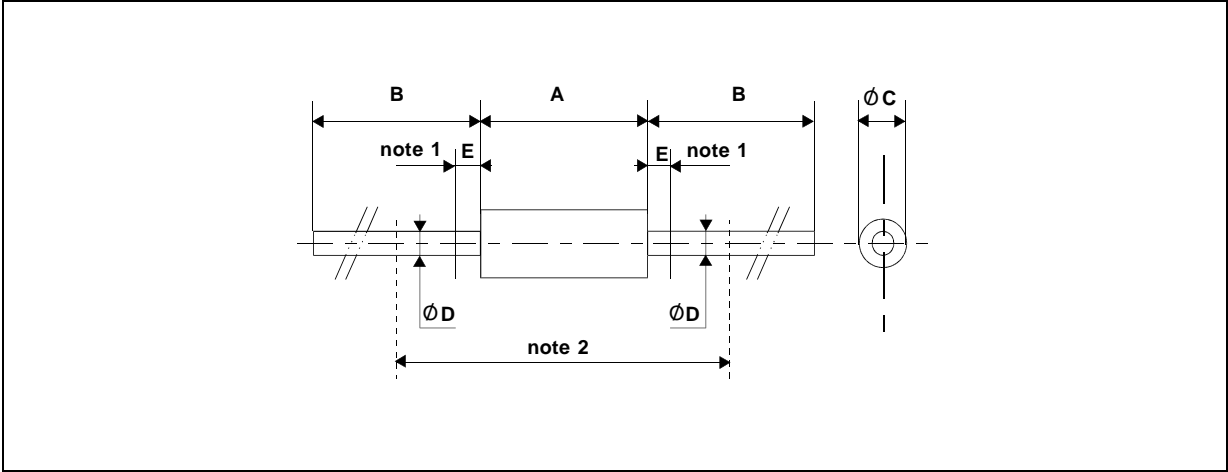
Figure 5. Capacitance C versus reverse applied voltage V_R (typical values).



BAT 41

PACKAGE MECHANICAL DATA

DO 35 Glass



| REF. | DIMENSIONS | | | | NOTES |
|------|-------------|-------|--------|-------|---|
| | Millimeters | | Inches | | |
| | Min. | Max. | Min. | Max. | |
| A | 3.050 | 4.500 | 0.120 | 0.117 | 1 - The lead diameter Ø D is not controlled over zone E 2 - The minimum axial length within which the device may be placed with its leads bent at right angles is 0.59"(15 mm) |
| B | 12.7 | | 0.500 | | |
| Ø C | 1.530 | 2.000 | 0.060 | 0.079 | |
| Ø D | 0.458 | 0.558 | 0.018 | 0.022 | |
| E | | 1.27 | | 0.050 | |

Cooling method : by convection and conduction
Marking: clear, ring at cathode end.
Weight: 0.15g